

General Description

The AO6602 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications.

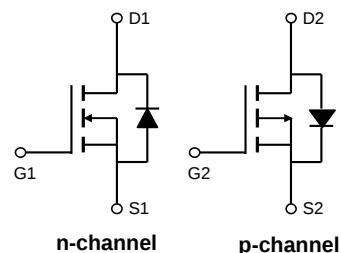
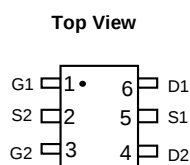
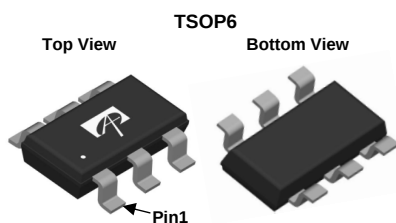
Product Summary

N-Channel

$V_{DS} = 30V$
 $I_D = 3.5A$ ($V_{GS}=10V$)
 $R_{DS(ON)} < 50m\Omega$ ($V_{GS}=10V$)
 $< 70m\Omega$ ($V_{GS}=4.5V$)

P-Channel

$-30V$
 $-2.7A$ ($V_{GS}=-10V$)
 $R_{DS(ON)} < 100m\Omega$ ($V_{GS}=-10V$)
 $< 170m\Omega$ ($V_{GS}=-4.5V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	3.5	-2.7	A
		3	-2.1	
Pulsed Drain Current ^C	I_{DM}	20	-15	
Power Dissipation ^B	P_D	1.15	1.15	W
		0.73	0.73	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	78	110	$^\circ C/W$
Maximum Junction-to-Ambient ^{A, D}		106	150	$^\circ C/W$
Maximum Junction-to-Lead	$R_{\theta JL}$	64	80	$^\circ C/W$

N-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.5	2	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3.5A T _J =125°C		40 61	50 77	mΩ
		V _{GS} =4.5V, I _D =2A		52	70	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3.5A		12		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.79	1	V
I _S	Maximum Body-Diode Continuous Current				1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		170	210	pF
C _{oss}	Output Capacitance			35		pF
C _{rss}	Reverse Transfer Capacitance			23		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.7	3.5	5.3	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =3.5A		4.05	5	nC
Q _g (4.5V)	Total Gate Charge			2	3	nC
Q _{gs}	Gate Source Charge			0.55		nC
Q _{gd}	Gate Drain Charge			1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =4.2Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			1.5		ns
t _{D(off)}	Turn-Off DelayTime			18.5		ns
t _f	Turn-Off Fall Time			15.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =3.5A, dI/dt=100A/μs		7.5	10	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3.5A, dI/dt=100A/μs		2.5		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

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N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

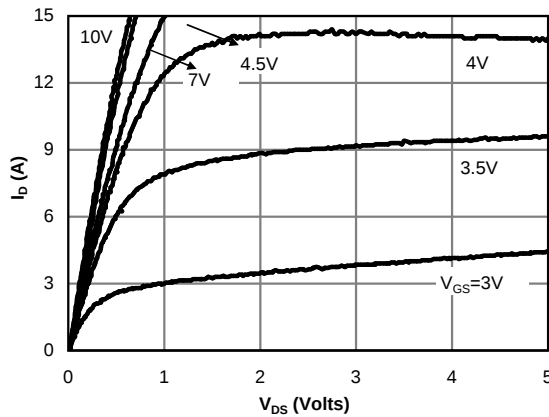


Fig 1: On-Region Characteristics (Note E)

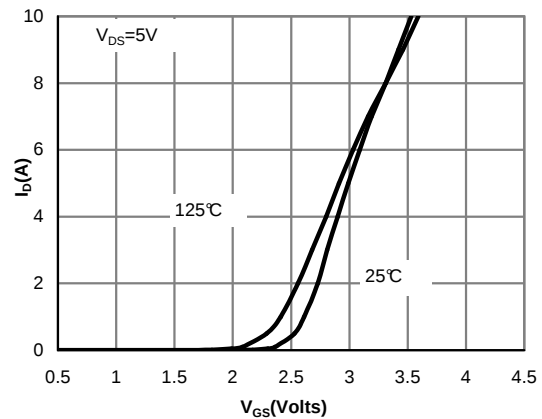


Figure 2: Transfer Characteristics (Note E)

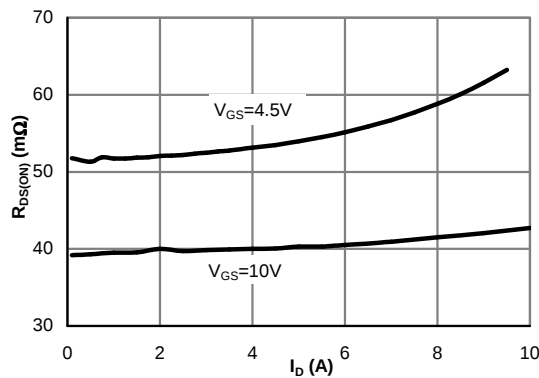


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

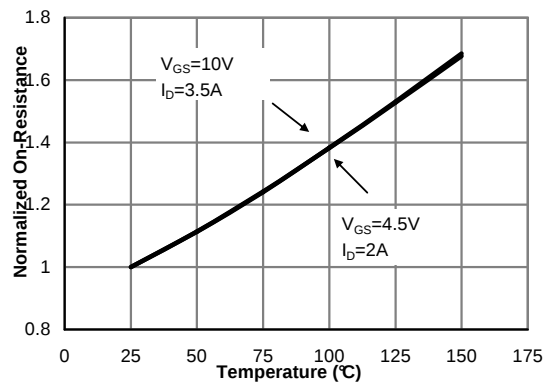


Figure 4: On-Resistance vs. Junction Temperature (Note E)

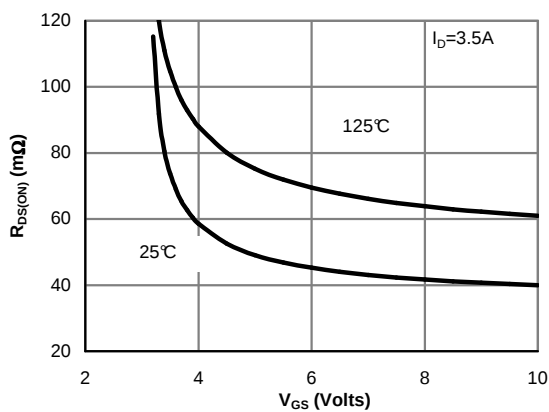


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

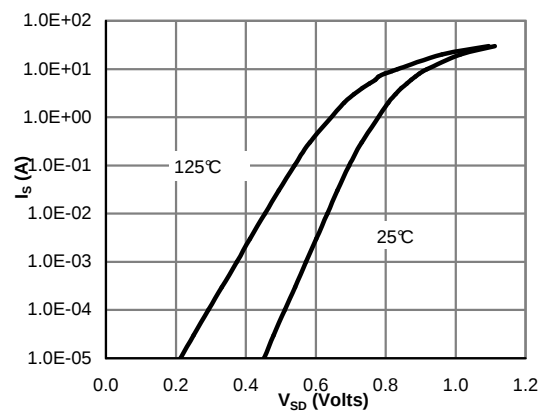
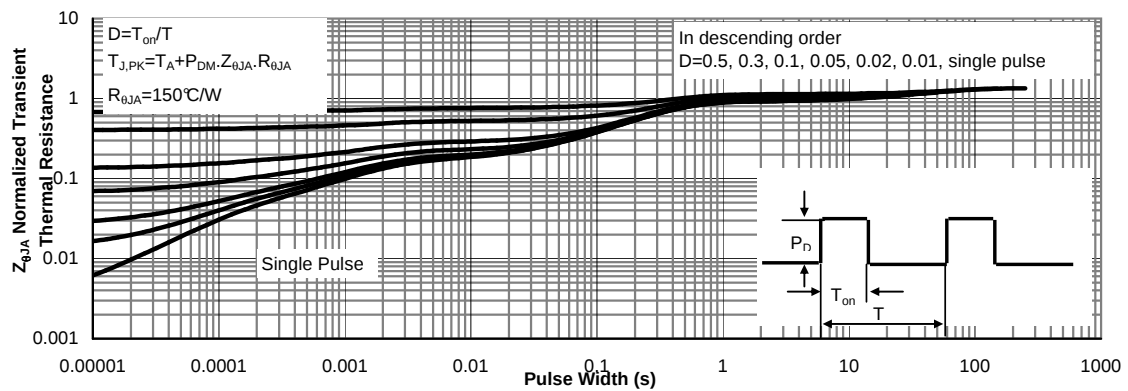
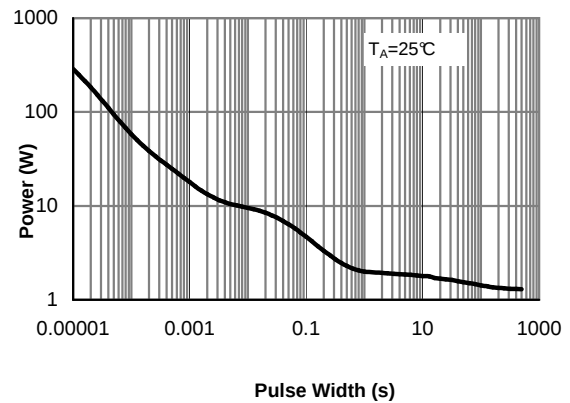
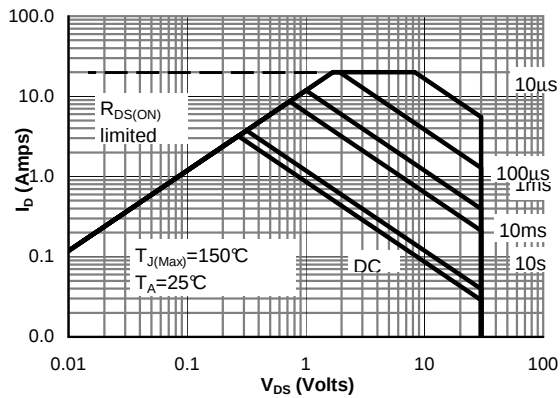
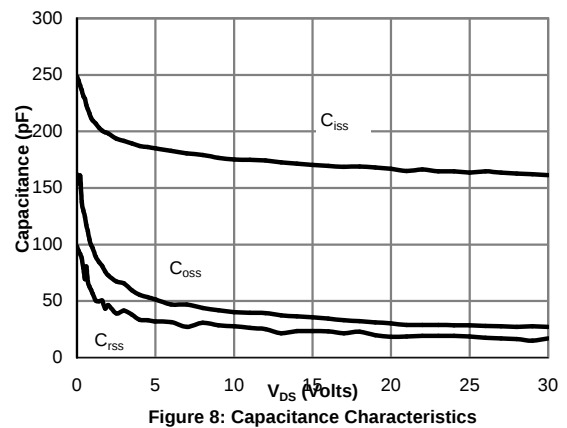
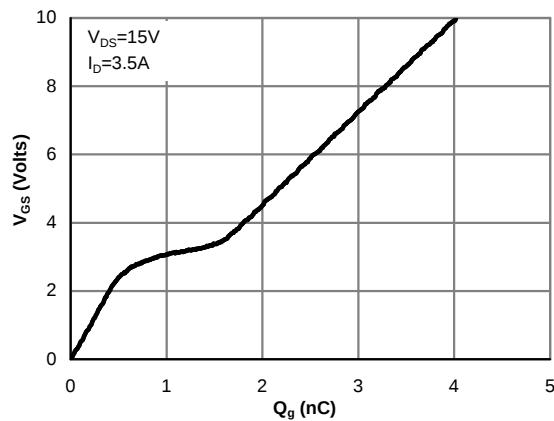
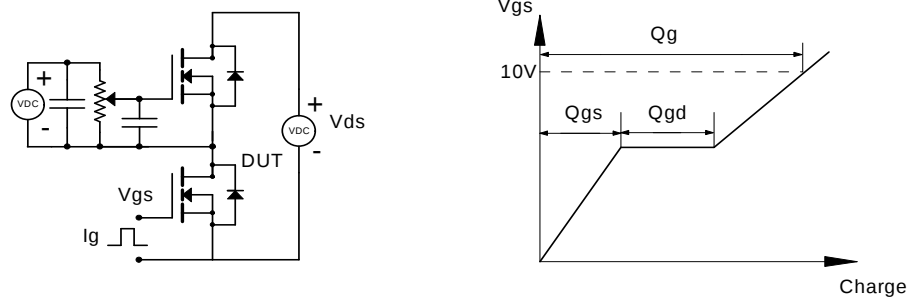


Figure 6: Body-Diode Characteristics (Note E)

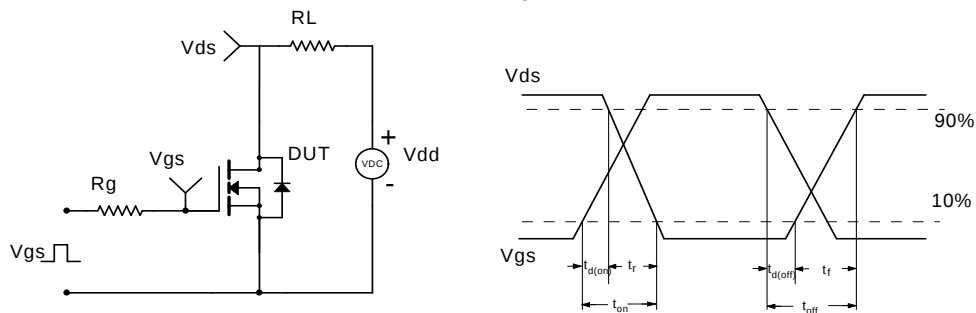
N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



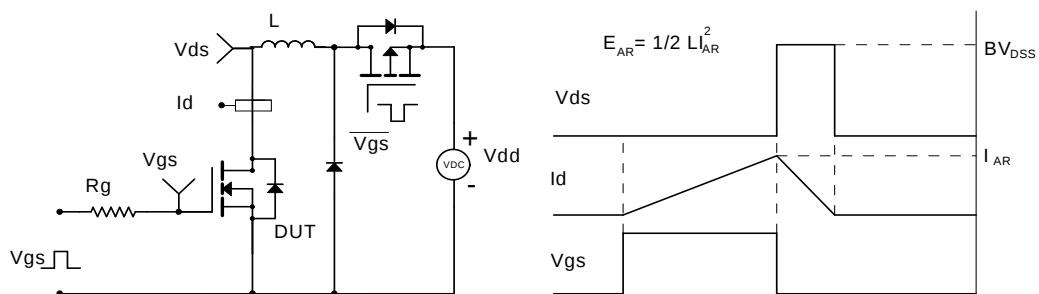
Gate Charge Test Circuit & Waveform



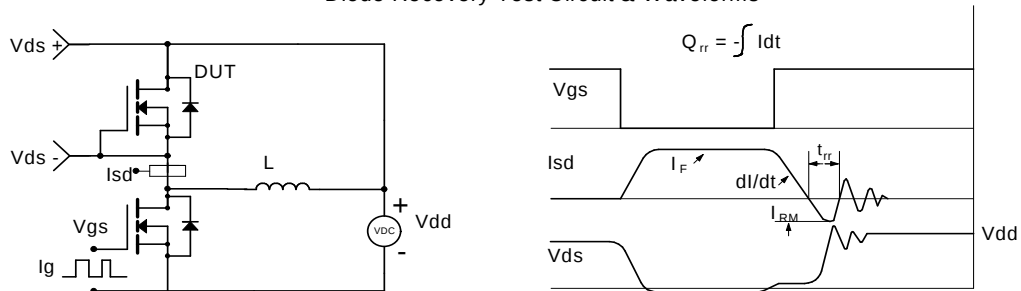
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.4	-1.9	-2.4	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-15			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-2.7A		82	100	mΩ
		T _J =125°C		115	140	
		V _{GS} =-4.5V, I _D =-2A		130	170	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-2.7A		5.5		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.8	-1	V
I _S	Maximum Body-Diode Continuous Current				-1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		197	240	pF
C _{oss}	Output Capacitance			42		pF
C _{rss}	Reverse Transfer Capacitance			26	37	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	3.5	7.2	11.0	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =-15V, I _D =2.7A		4.3	5.2	nC
Q _g (4.5V)	Total Gate Charge			2.2	3	nC
Q _{gs}	Gate Source Charge			0.7		nC
Q _{gd}	Gate Drain Charge			1.1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =-15V, R _L =5.55Ω, R _{GEN} =3Ω		7.5		ns
t _r	Turn-On Rise Time			4.1		ns
t _{D(off)}	Turn-Off DelayTime			11.8		ns
t _f	Turn-Off Fall Time			3.8		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-2.7A, dI/dt=100A/μs		11.3	14	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-2.7A, dI/dt=100A/μs		4.4		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

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P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

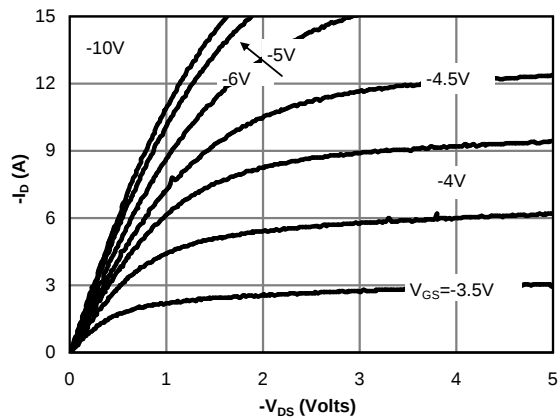


Figure 1: On-Region Characteristics (Note E)

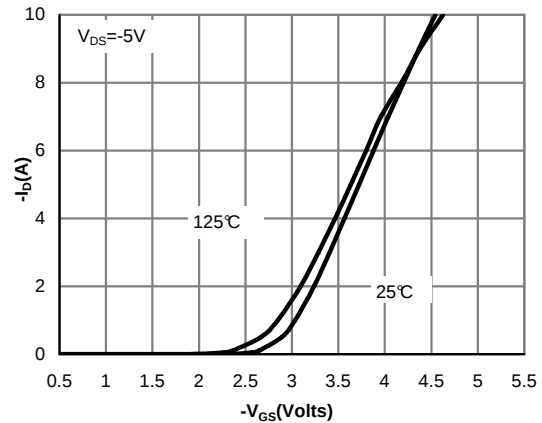


Figure 2: Transfer Characteristics (Note E)

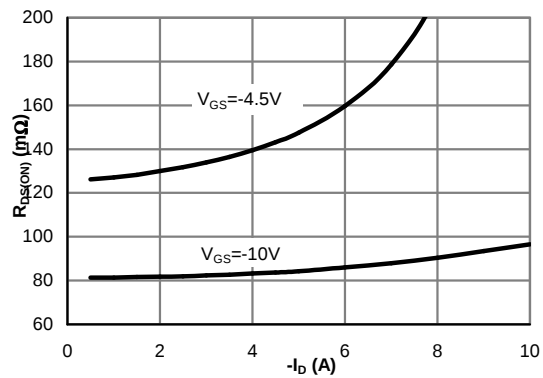


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

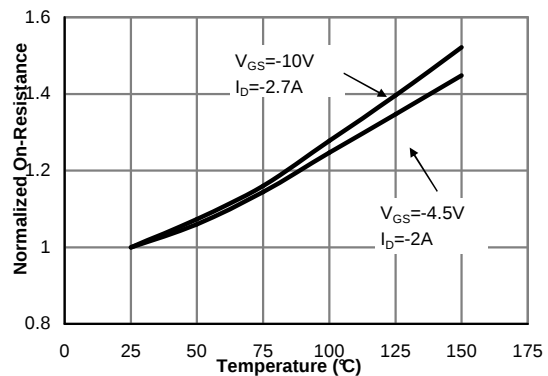


Figure 4: On-Resistance vs. Junction Temperature (Note E)

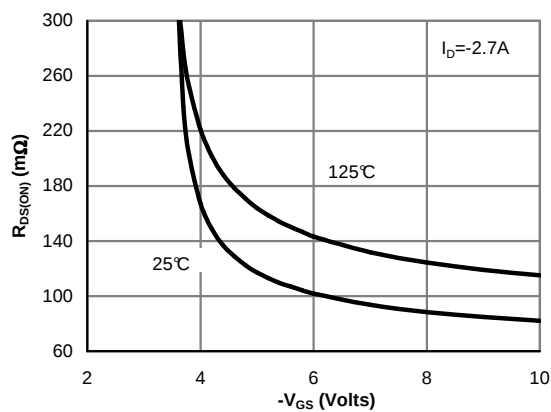


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

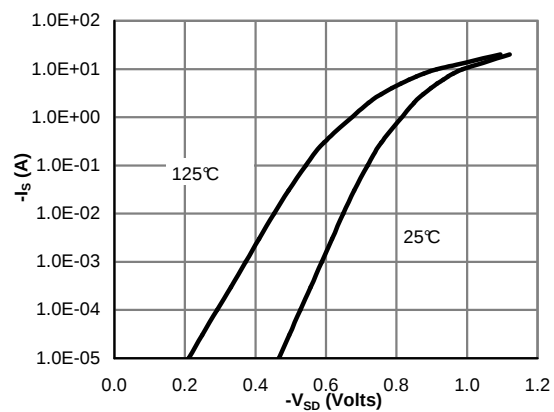


Figure 6: Body-Diode Characteristics (Note E)

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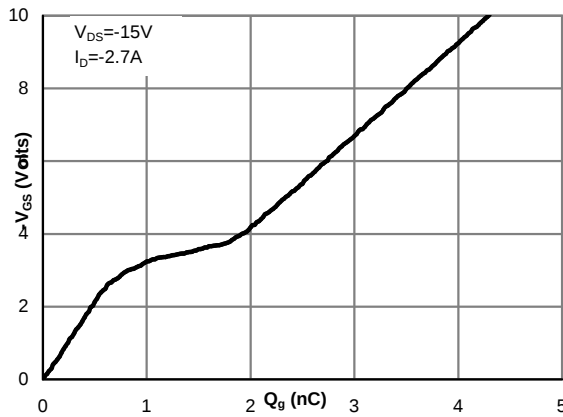


Figure 7: Gate-Charge Characteristics

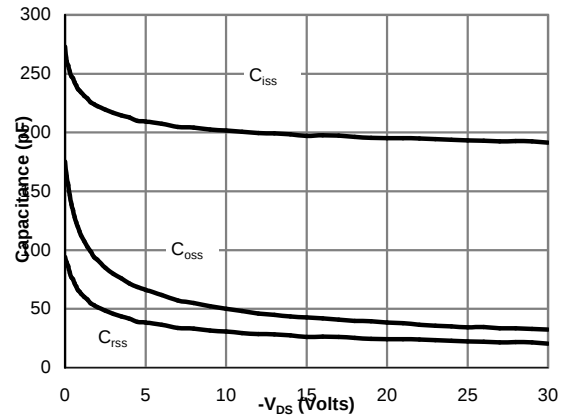


Figure 8: Capacitance Characteristics

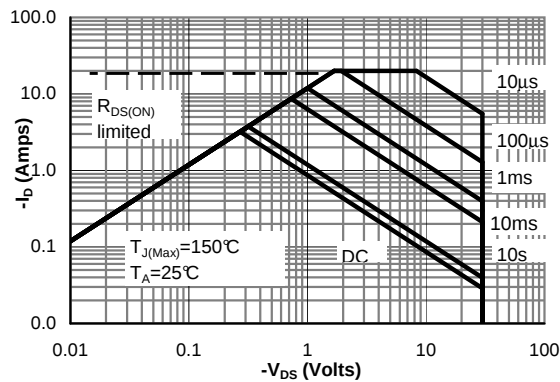


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

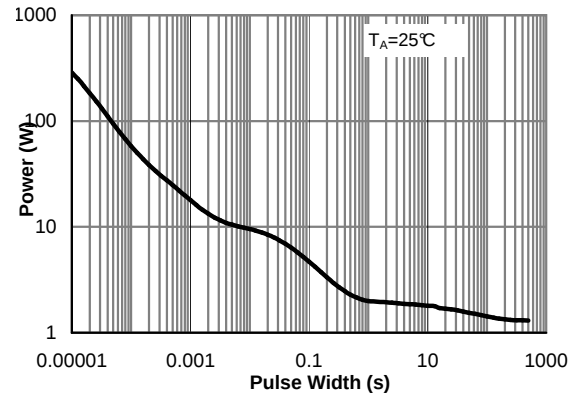


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

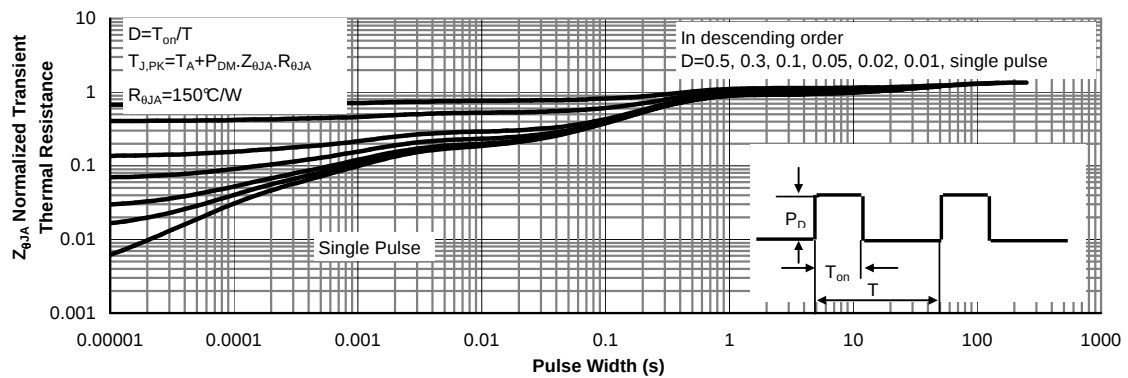
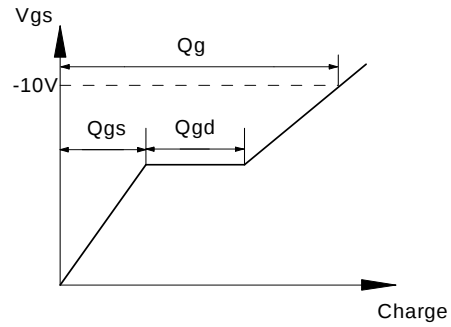
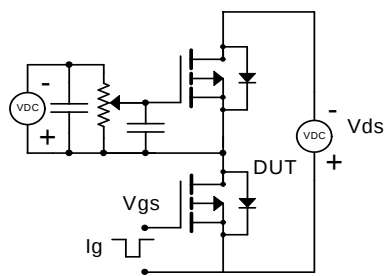
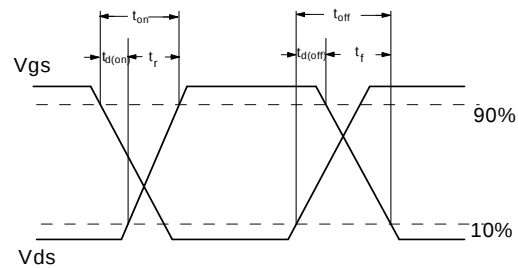
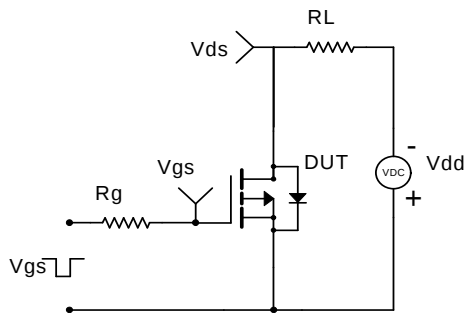


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

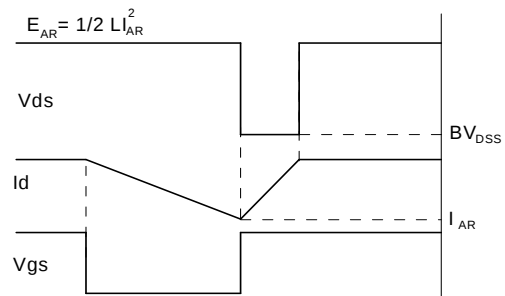
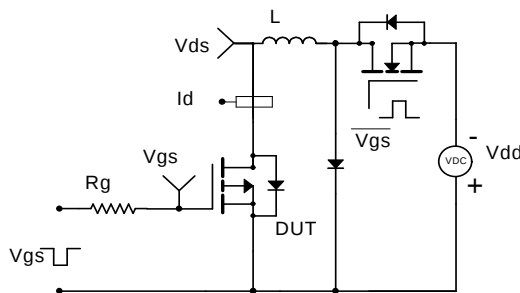
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

